TGBR40S80C DIODE

# DUAL TRENCH MOS SCHOTTKY BARRIER RECTIFIER

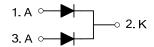
#### **■** DESCRIPTION

The UTC **TGBR40S80C** is a dual trench mos schottky barrier rectifier, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

#### ■ FEATURES

- \* Super low forward voltage drop
- \* High switching speed

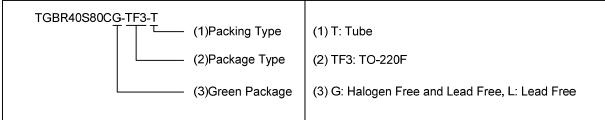




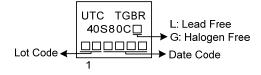
## ■ ORDERING INFORMATION

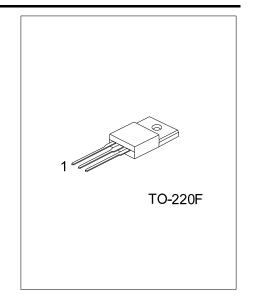
Ordering Number		Daakana	Pin Assignment			De alcin a	
Lead Free	Halogen Free	Package	1	2	3	Packing	
TGBR40S80CL-TF3-T	TGBR40S80CG-TF3-T	TO-220F	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



#### ■ MARKING





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# ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT	
DC Blocking Voltage		$V_{RM}$	80	V	
Average Rectified Output Current	Per Leg		20	Α	
(T <sub>C</sub> =140°C)	Total	Io	40	Α	
Non-Repetitive Peak Forward Surge Current 8.3ms			120	А	
Single Half Sine-Wave Superimposed on Rated Load		IFSM	120		
Operating Junction Temperature		TJ	-65 ~ <b>+</b> 150	°C	
Storage Temperature		T <sub>STG</sub>	-65 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL CHARACTERISTICS (PER LEG)**

PARAMETER	SYMBOL	RATINGS	UNIT	
Typical Thermal Resistance	θјс	2	°C/W	

# ■ ELECTRICAL CHARACTERISTICS (PER LEG) (TA=25°C, unless otherwise specified.)

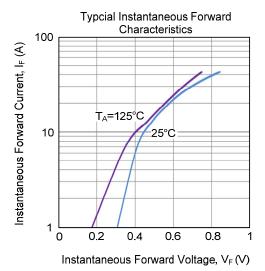
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	$V_{(BR)R}$	I <sub>R</sub> =0.5mA	80			V
Familiard Voltage Duag	V <sub>FM</sub>	I <sub>F</sub> =20A, T <sub>J</sub> =25°C		0.58	0.65	V
Forward Voltage Drop		I <sub>F</sub> =20A, T <sub>J</sub> =125°C			0.62	٧
Leakage Current	I <sub>RM</sub>	V <sub>R</sub> =80V, T <sub>J</sub> =25°C			100	μΑ
		V <sub>R</sub> =80V, T <sub>J</sub> =125°C			10	mΑ

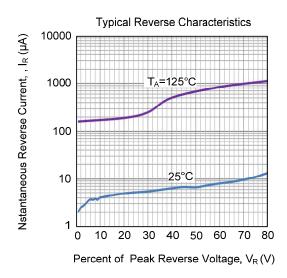
Notes: 1. Short duration pulse test used to minimize self-heating effect.

<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

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#### ■ TYPICAL CHARACTERISTICS





UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.